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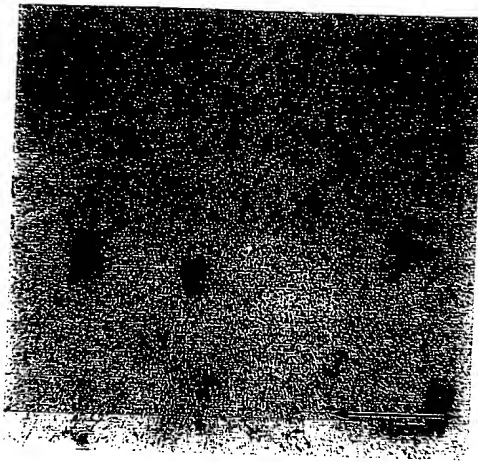
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3910  
Fig. 1A

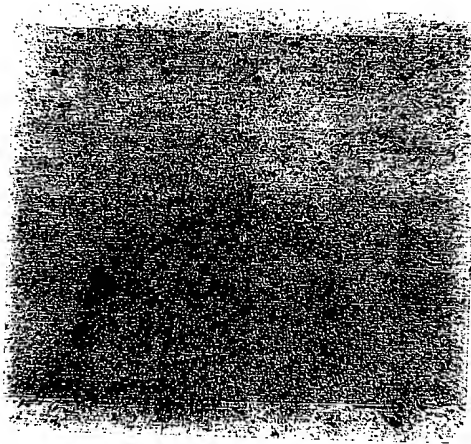


Fig. 1B

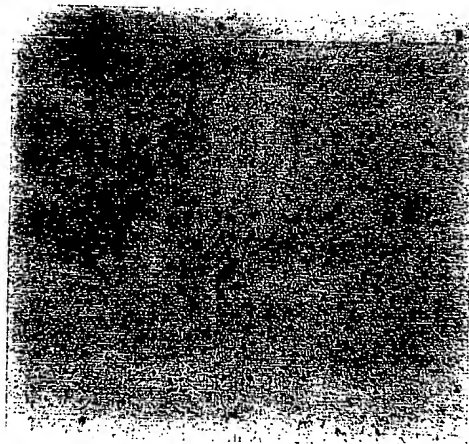


Fig. 1C



Fig. 2A



Fig. 2B

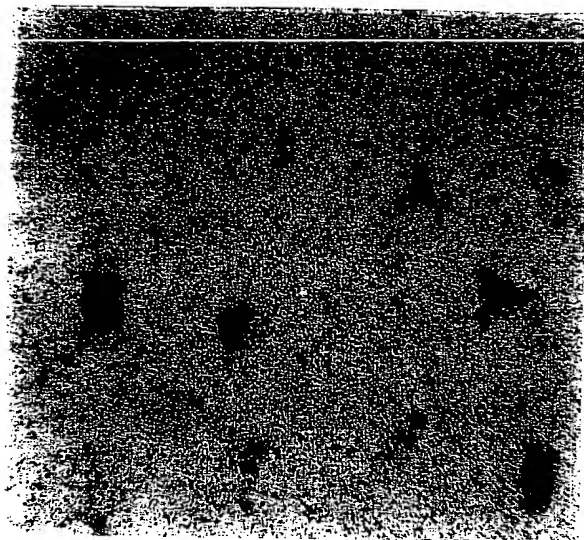


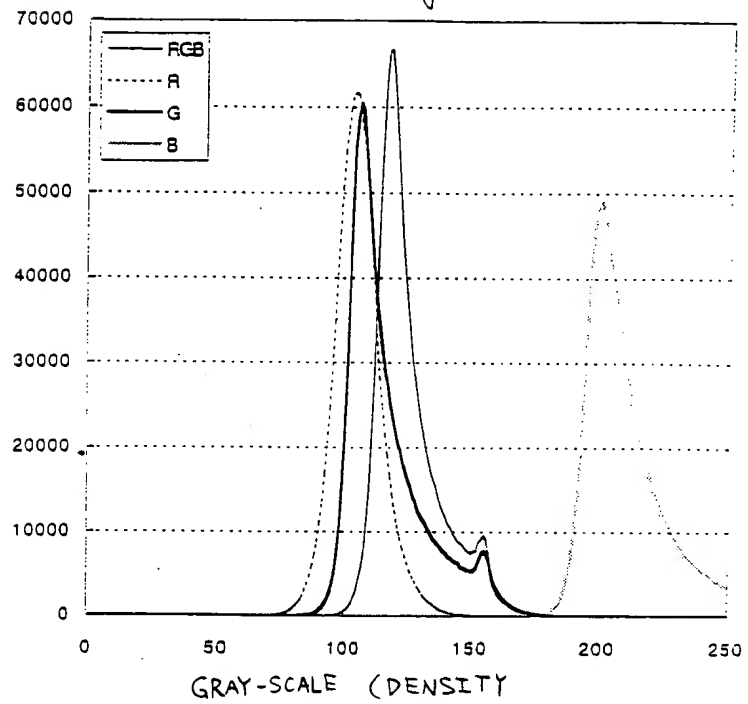
Fig. 3A



Fig. 3B



Fig. 4



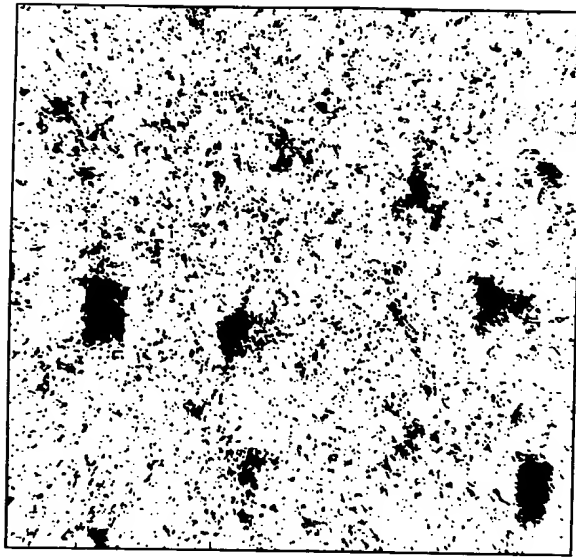


Fig. 5A

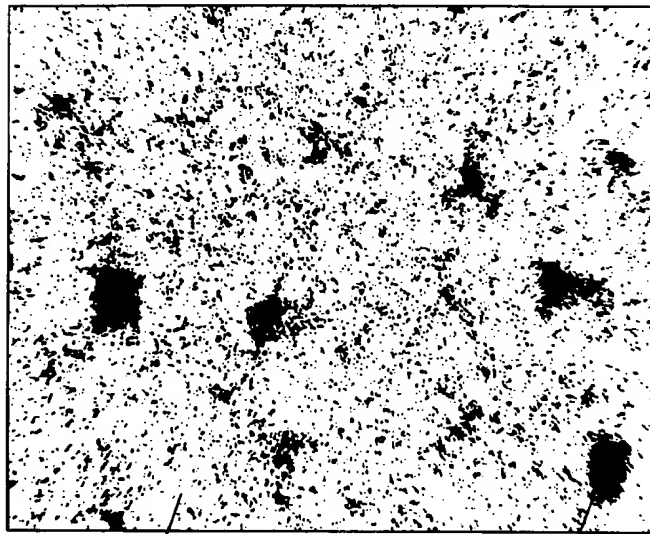
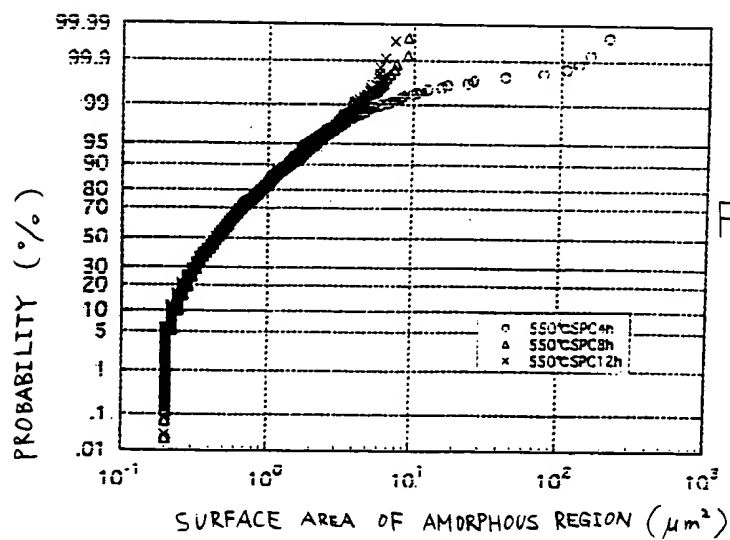
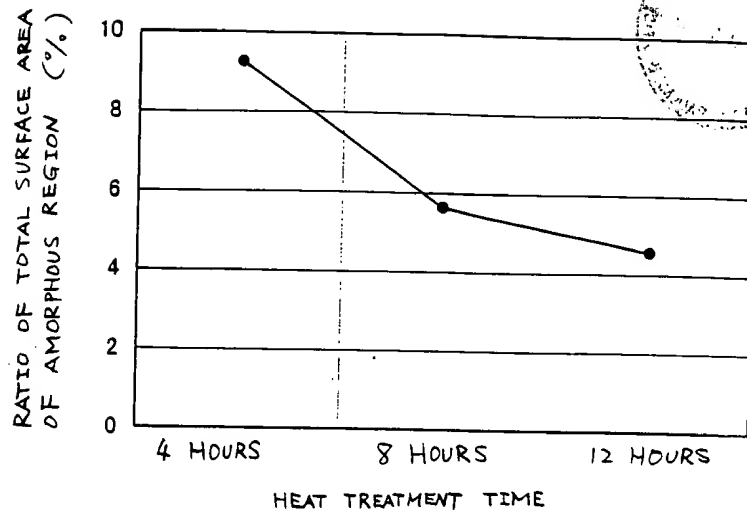


Fig. 5B

5001

5002



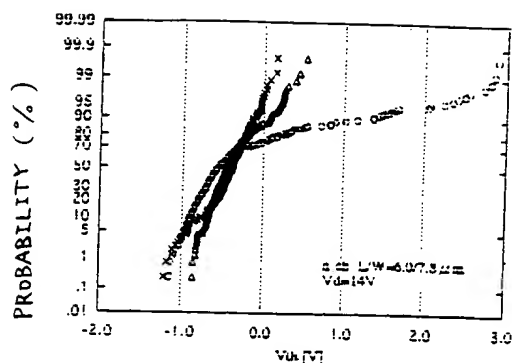


Fig. 7A

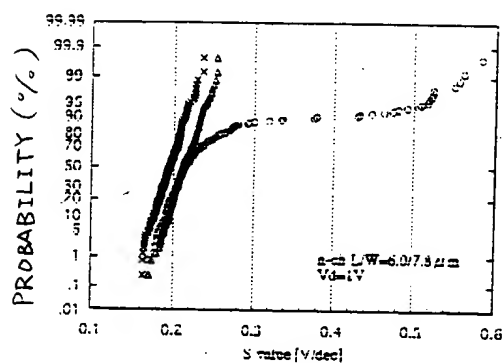


Fig. 7B

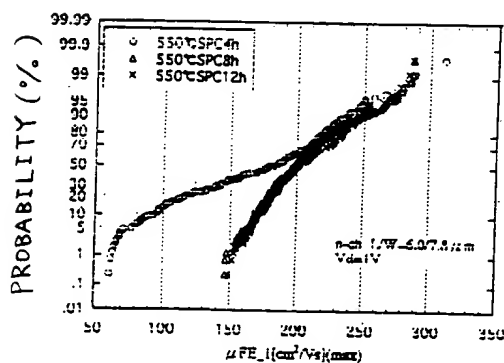


Fig. 7c



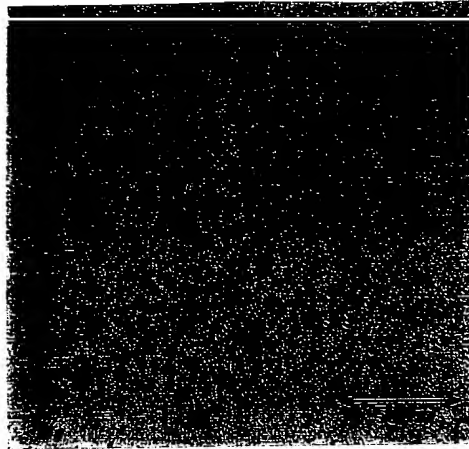


Fig. 8A

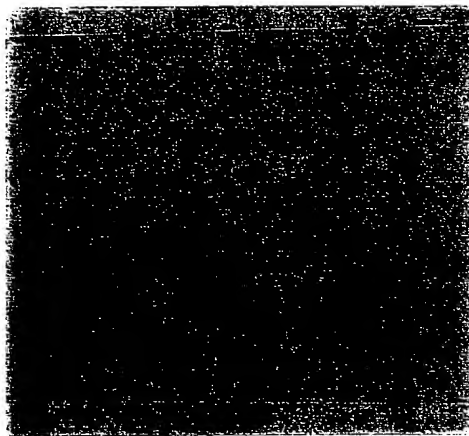


Fig. 8B

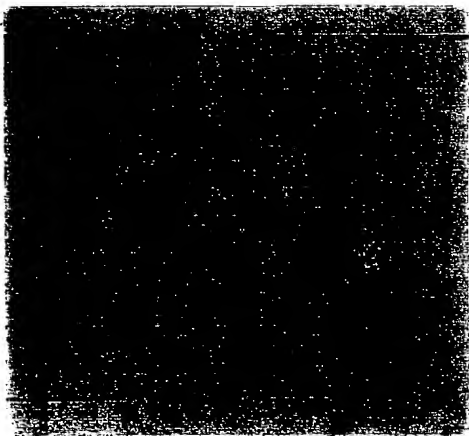
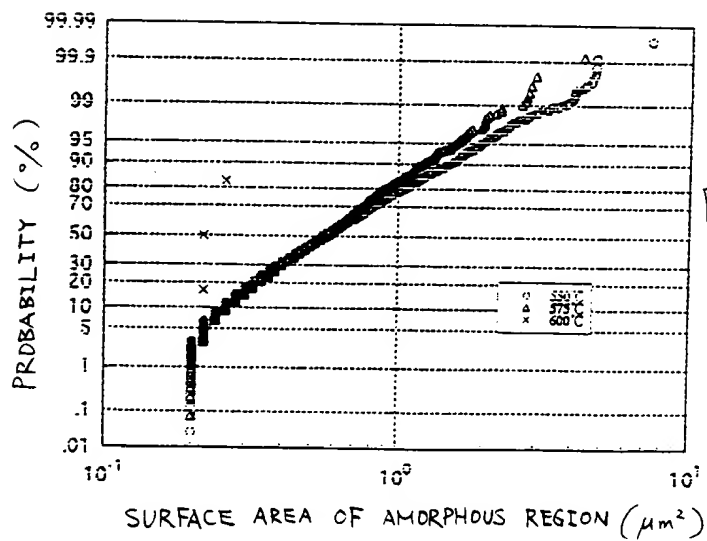
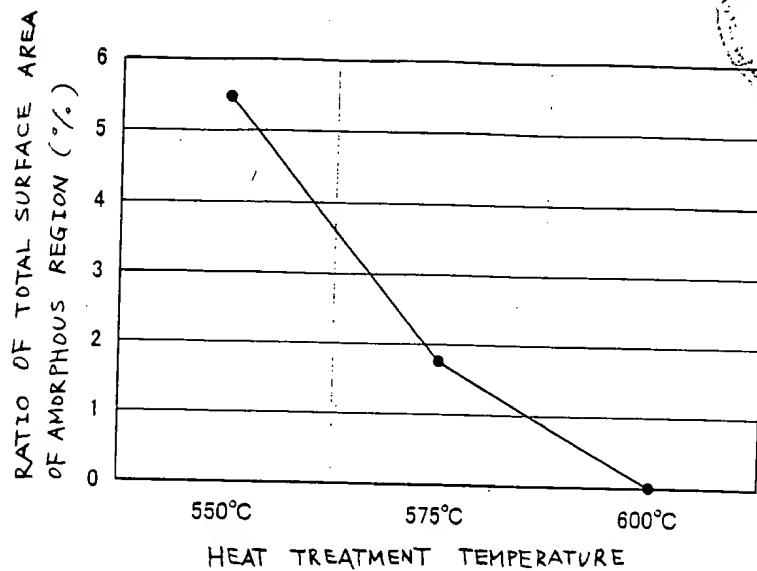


Fig. 8C



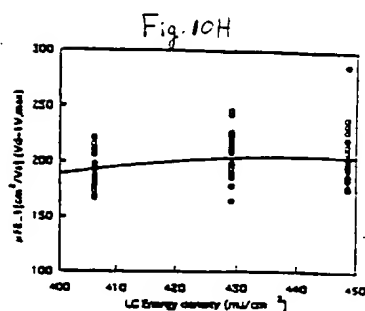
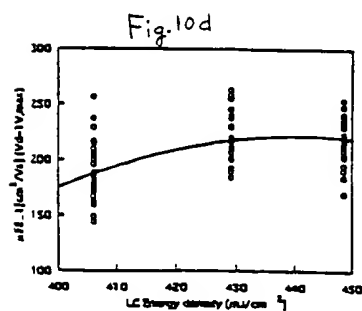
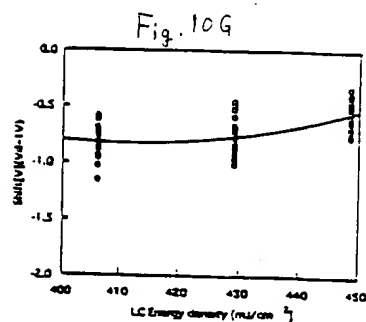
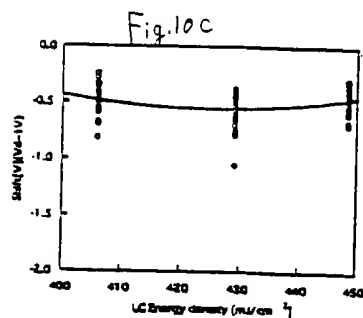
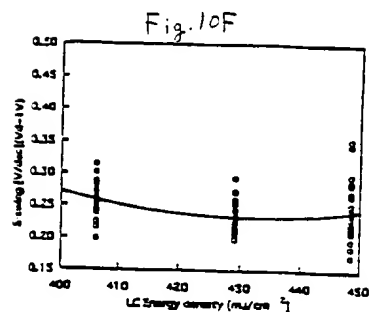
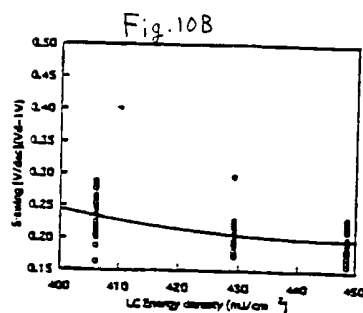
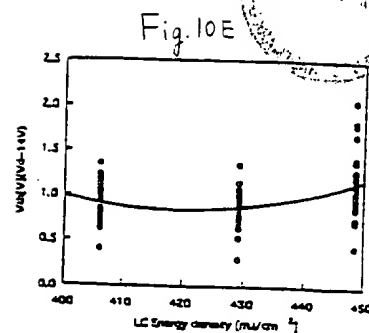
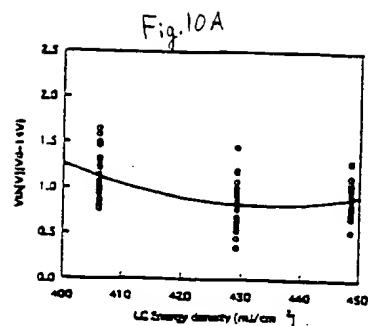


Fig. 11A

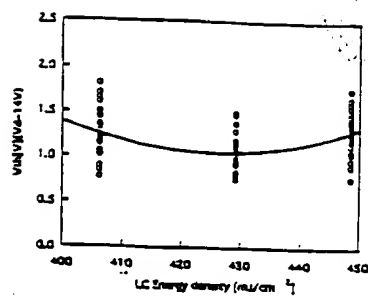


Fig. 11B

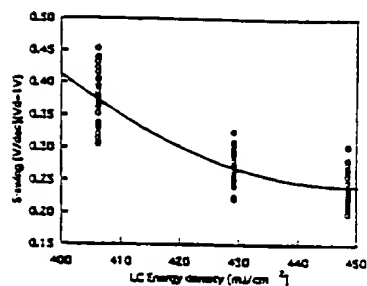


Fig. 11c

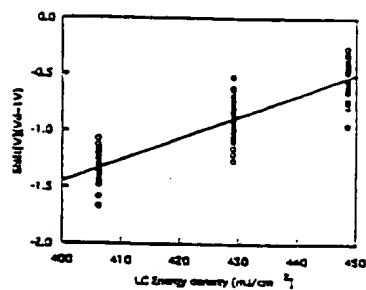
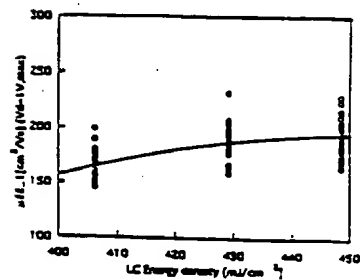
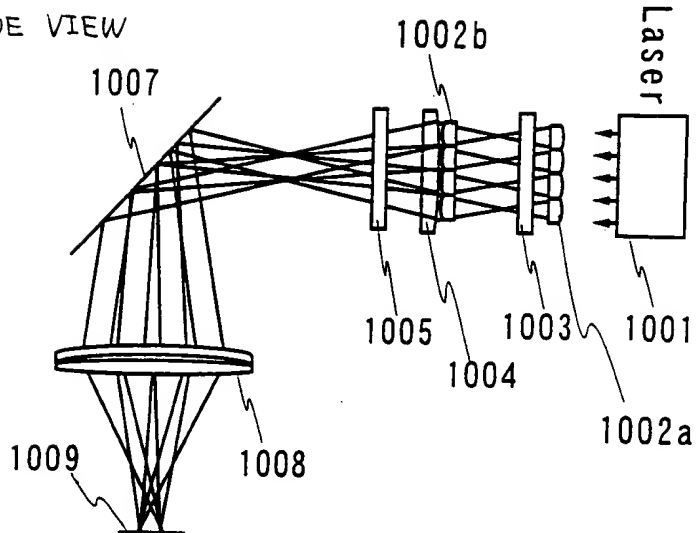


Fig. 11d



SIDE VIEW



TOP VIEW

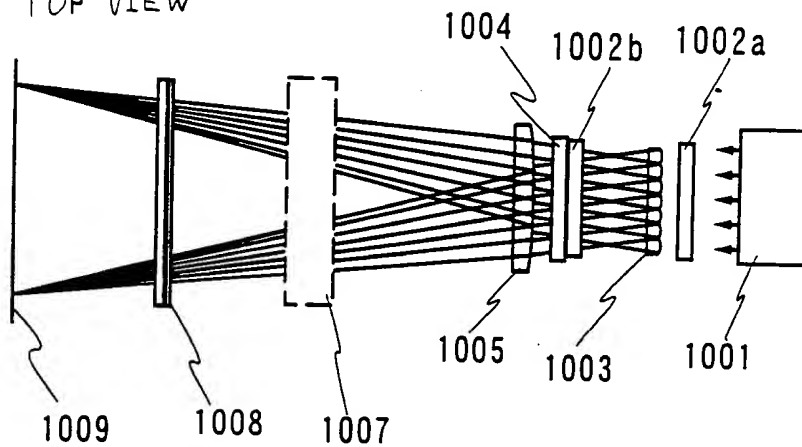
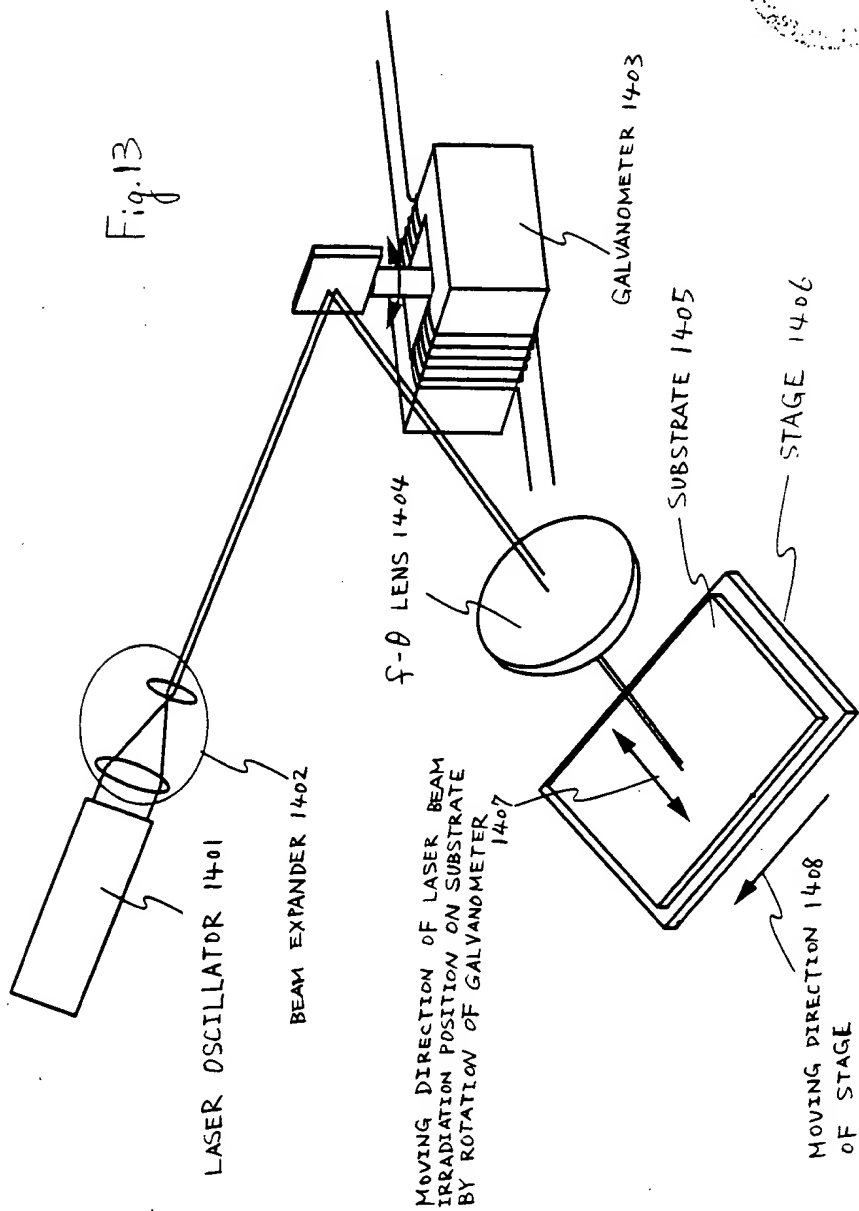
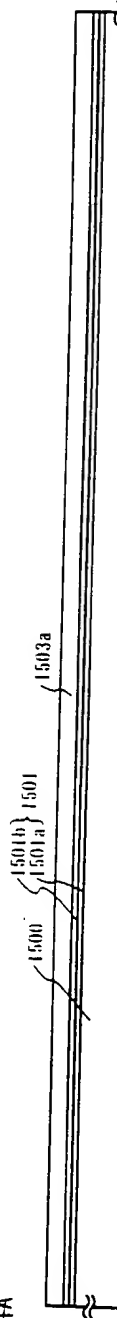


Fig. 12



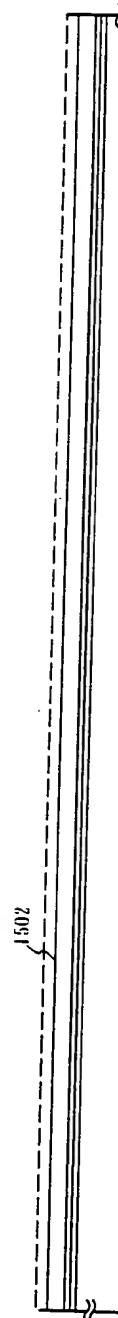
# STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

Fig. 14A



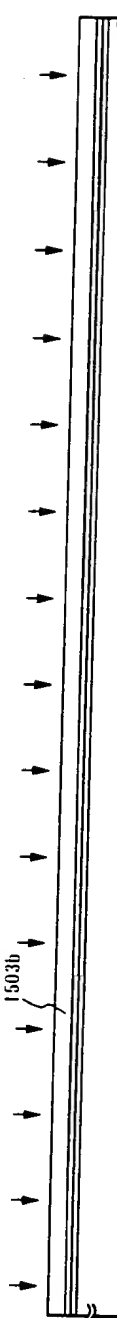
# FORMATION OF METAL CONTAINING LAYER / HEAT TREATMENT

Fig. 14B



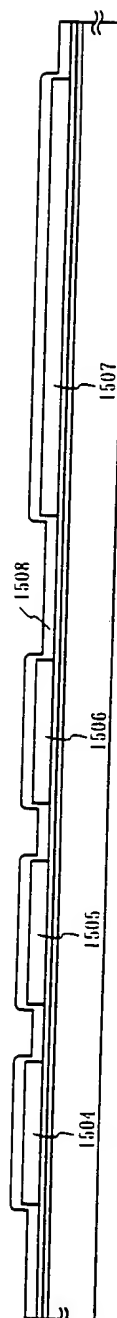
# LASER BEAM IRRADIATION

Fig. 14C



# STEP OF FORMING MASK LAYER

Fig. 14D



# CHANNEL DOPE STEP

Fig. 14E

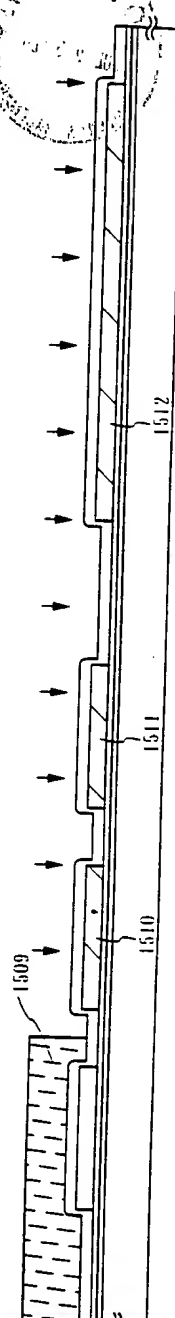


Fig. 15A  $n^-$  DOPE STEP

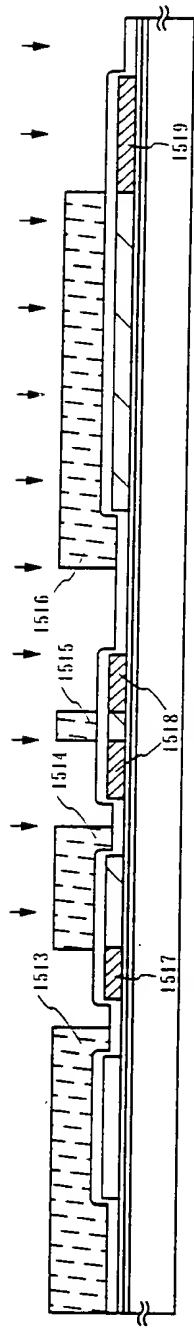


Fig. 15B STEP OF REMOVING MASK LAYER/LASER ACTIVATION STEP/STEP OF FORMING GATE INSULATING FILM

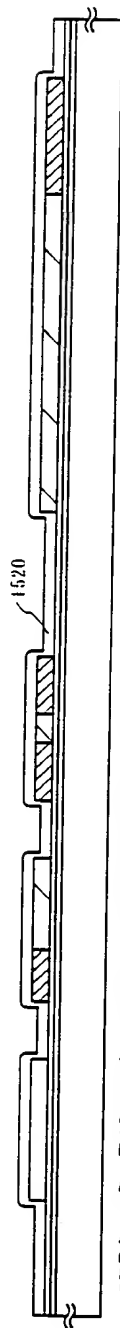


Fig. 15C STEP OF FORMING FIRST CONDUCTIVE LAYER

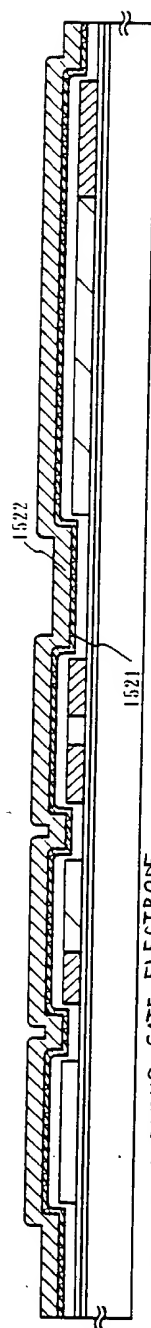
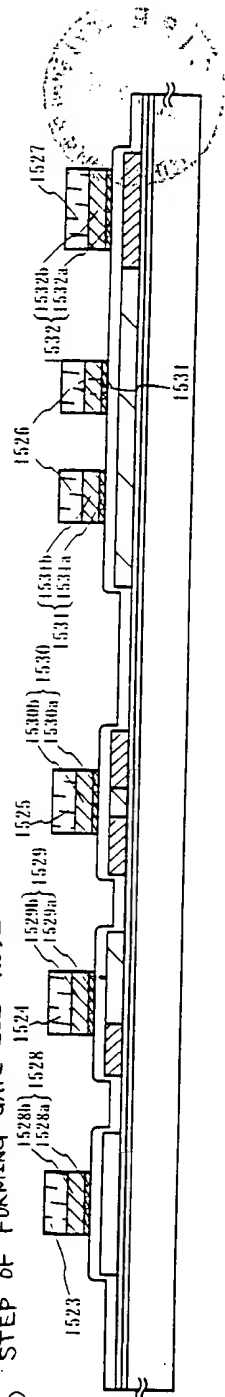
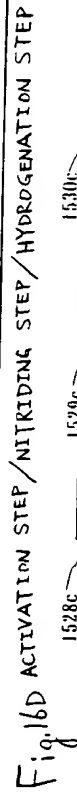
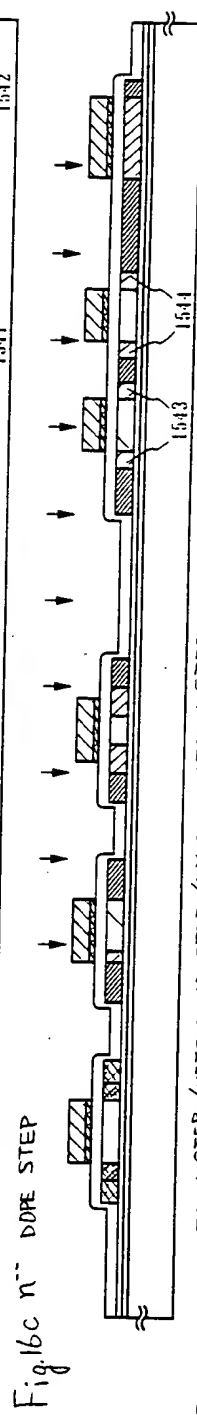
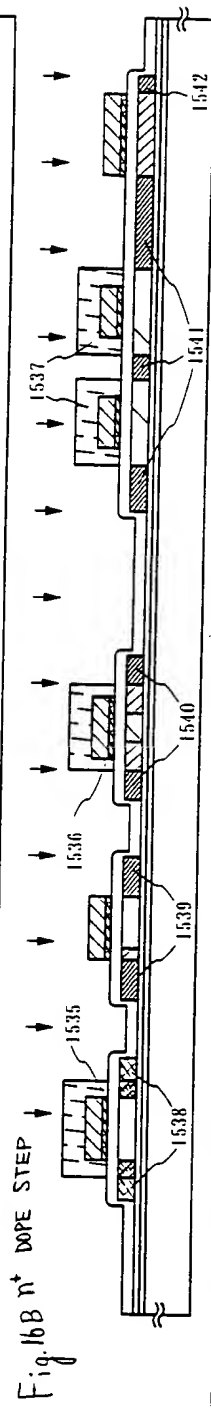
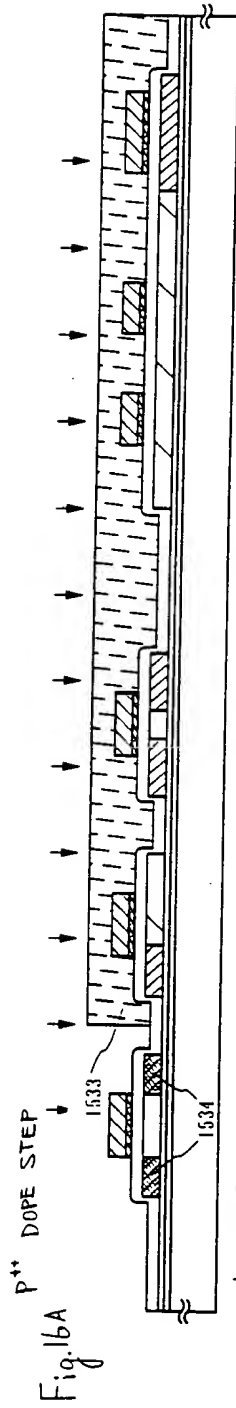


Fig. 15D STEP OF FORMING GATE ELECTRODE

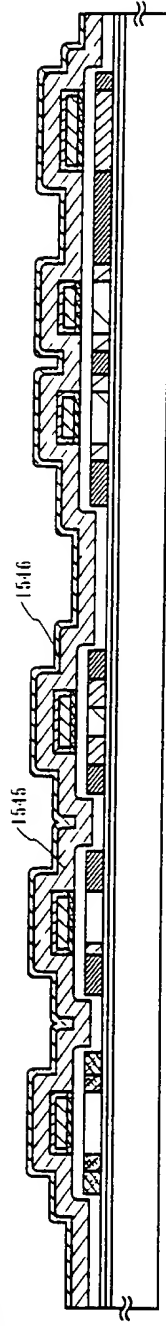






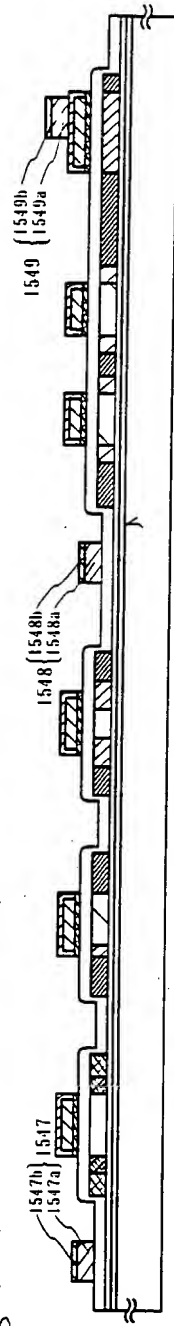
STEP OF FORMING SECOND CONDUCTIVE FILM

Fig. 17A



FORMATION OF GATE WIRING

Fig. 17B



STEP OF FORMING INTERLAYER INSULATING FILM/STEP OF FORMING CONTACT HOLE/STEP OF FORMING WIRING/STEP OF FORMING PASSIVATION FILM

Fig. 17C

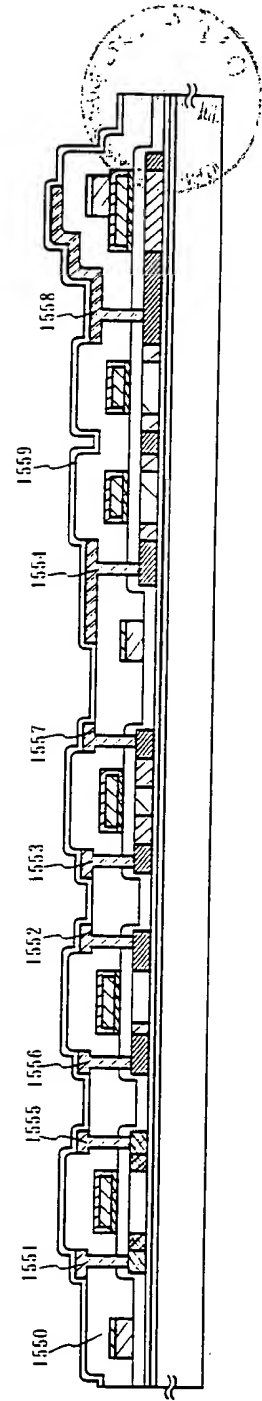
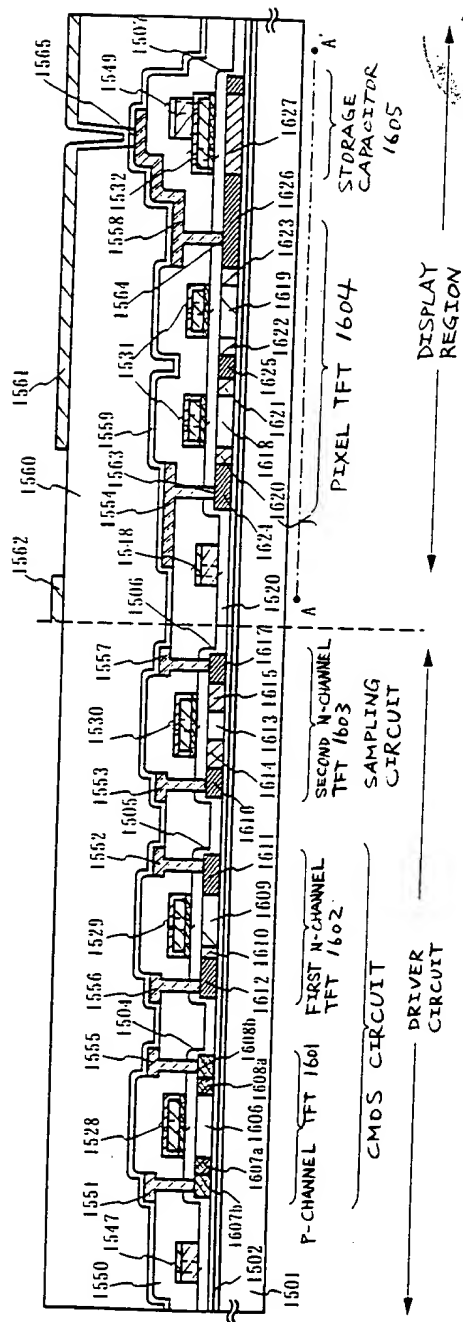


Fig. 18

STEP OF FORMING RESIN FILM/ STEP OF FORMING CONTACT HOLE/  
STEP OF FORMING PIXEL ELECTRODE



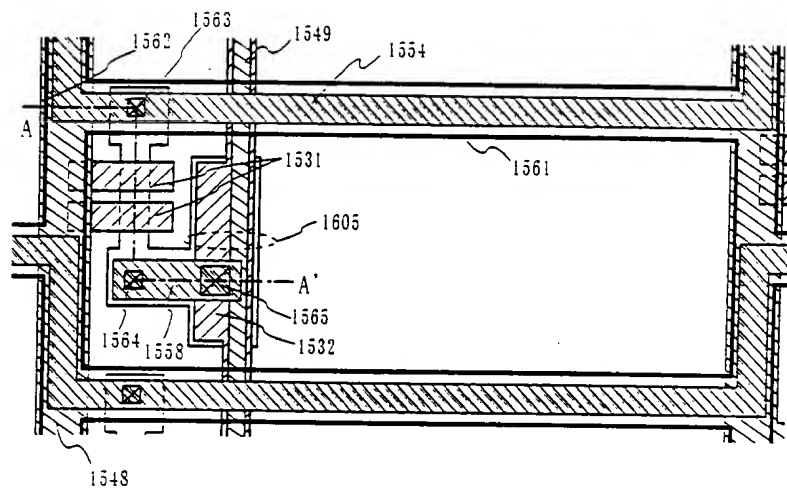


Fig. 19

Fig. 20

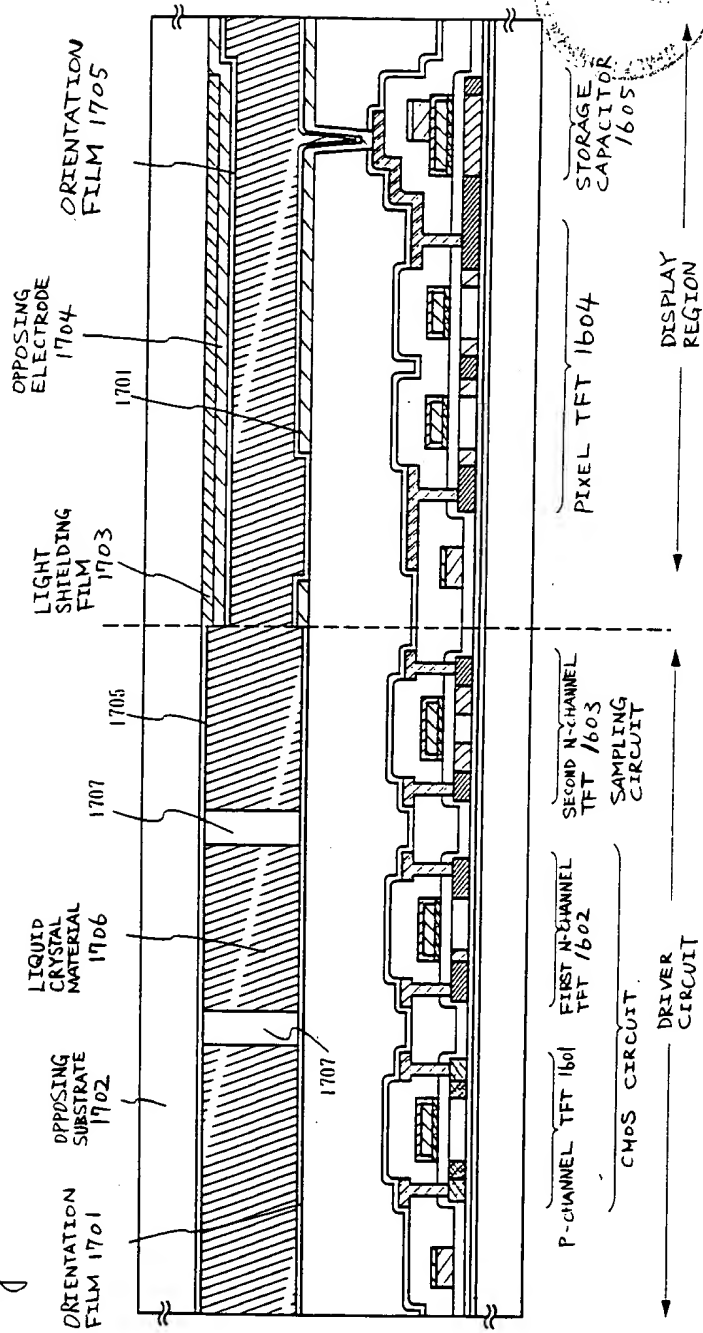


Fig. 21A

STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

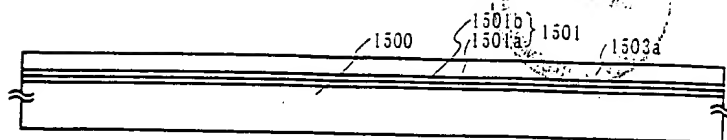


Fig. 21B

STEP OF ADDING CATALYTIC ELEMENT

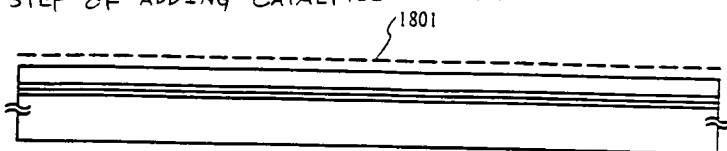


Fig. 21C

LASER ANNEALING STEP

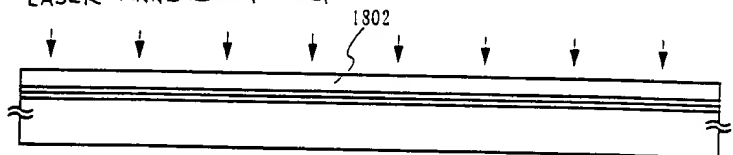


Fig. 22A

STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

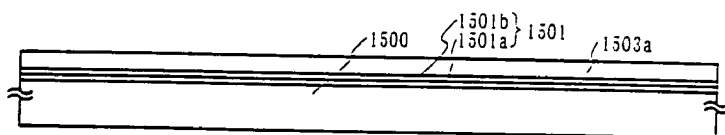


Fig. 22B

STEP OF ADDING CATALYTIC ELEMENT

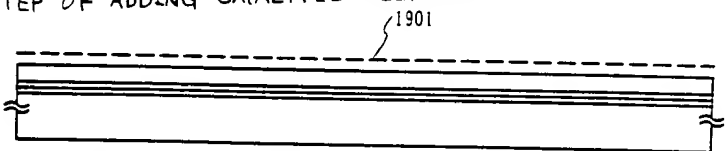


Fig. 22C

CRYSTALLIZATION STEP (HEAT CRYSTALLIZATION)

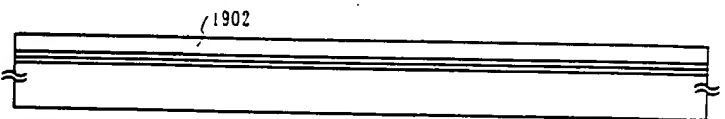


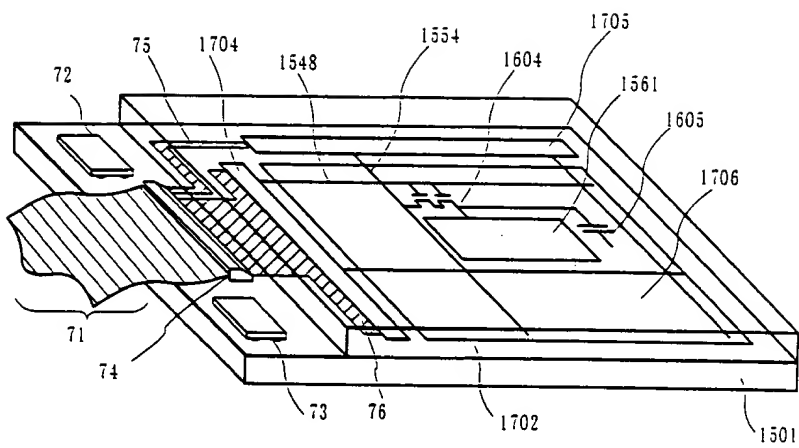
Fig. 22D

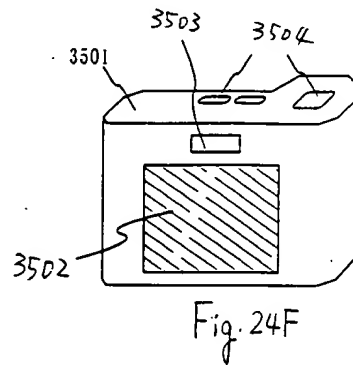
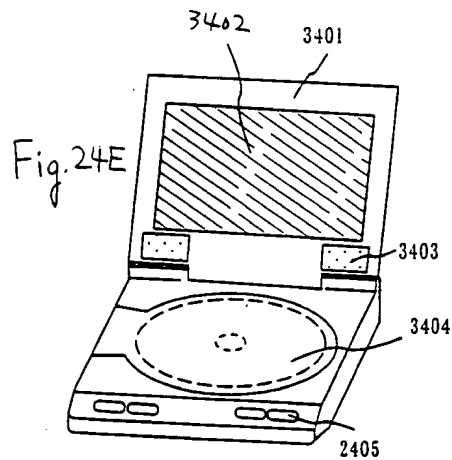
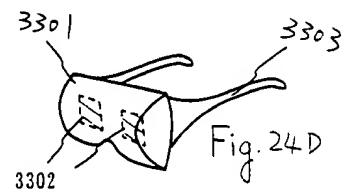
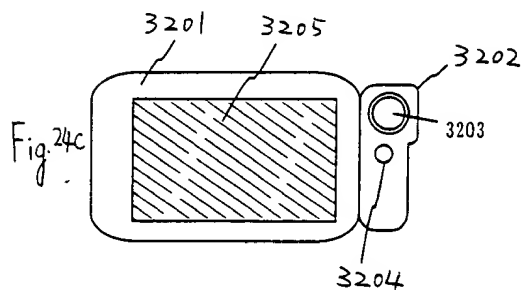
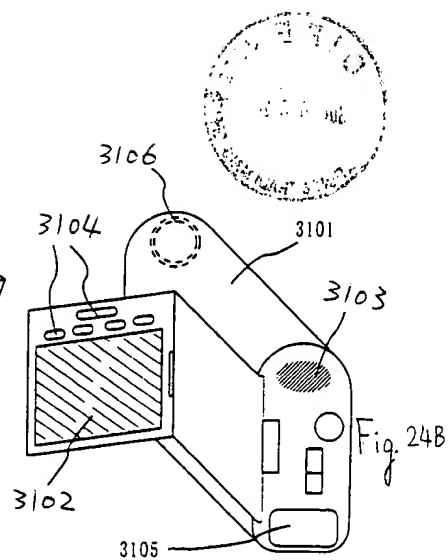
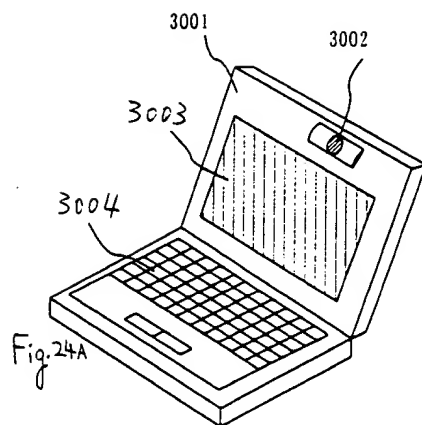
LASER ANNEALING STEP



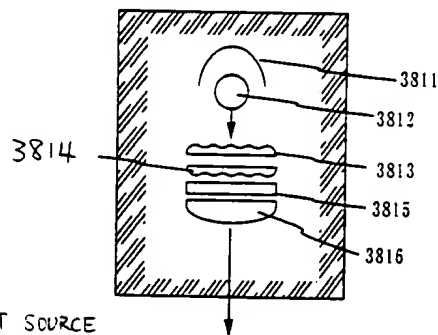
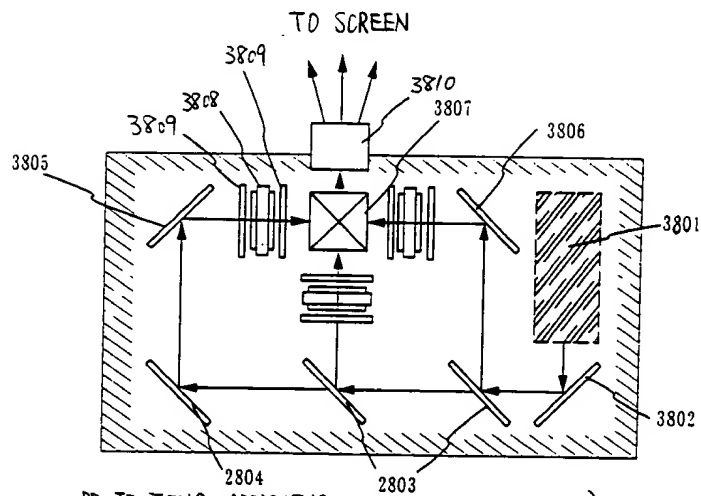
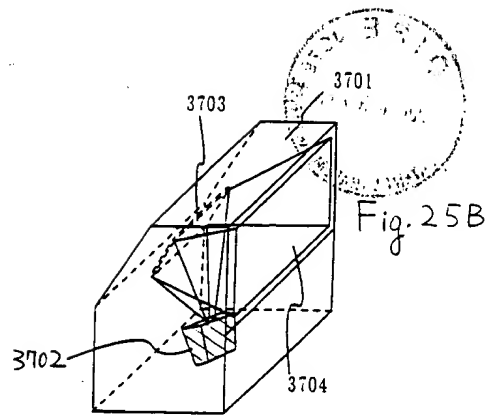
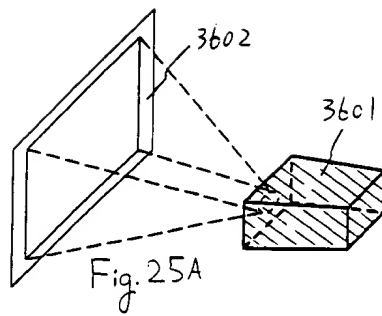


Fig. 23









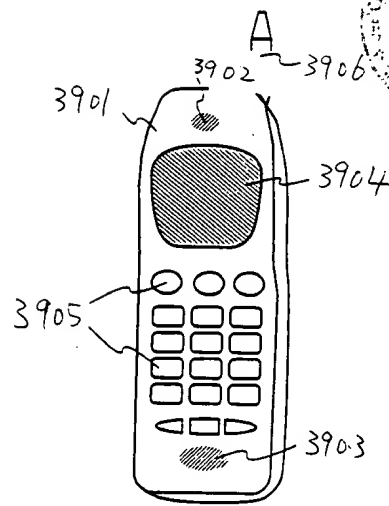


Fig. 26A

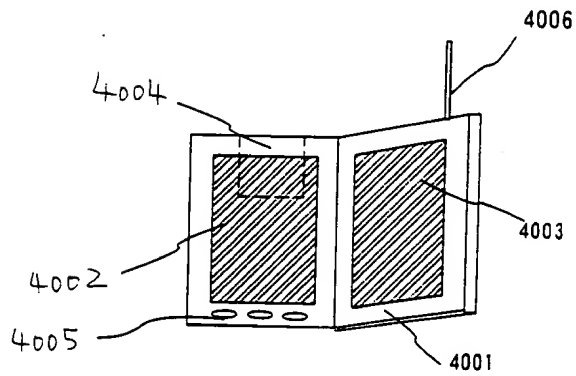


Fig. 26B

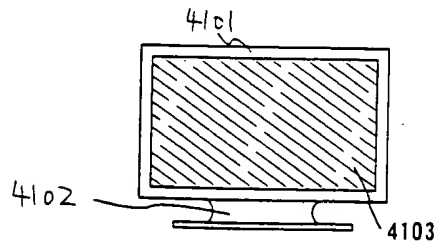


Fig. 26C